

New Jersey Semi-Conductor Products, Inc.

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1N2620, A, B (SILICON) thru 1N2624, A, B

Temperature-compensated zener reference diodes utilizing an oxide-passivated junction for long-term voltage stability. Construction consists of welded hermetically sealed metal and glass case.

MAXIMUM RATINGS

Junction Temperature: -55 to $+175^{\circ}\text{C}$

Storage Temperature: -65 to $+175^{\circ}\text{C}$

DC Power Dissipation: 750 mW @ $T_A = 25^{\circ}\text{C}$

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, welded metal and glass

DIMENSIONS: See outline drawing.

FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.

POLARITY: Cathode to case

WEIGHT: 1.5 Grams (approx)

MOUNTING POSITION: Any

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

JEDEC Type No.	Maximum Voltage Change ΔV_Z (Volts) (Note 1)	Ambient Test Temperature $^{\circ}\text{C}$ $\pm 1^{\circ}\text{C}$	Temperature Coefficient $\%/^{\circ}\text{C}$ (Note 1)	Maximum Dynamic Impedance Z_{ZT} (Ohms) (Note 2)
$V_Z = 9.3\text{ V} \pm 5.0\% * @ I_{ZT} = 10\text{ mA}$				
1N2620	0.070	0, ± 25 , ± 75	0.01	15
1N2621	0.035		0.005	
1N2622	0.014		0.002	
1N2623	0.007		0.001	
1N2624	0.003		0.0005	
1N2620A	0.144	-55 , 0, ± 25 , ± 75 , ± 100	0.01	15
1N2621A	0.072		0.005	
1N2622A	0.029		0.002	
1N2623A	0.014		0.001	
1N2624A	0.007		0.0005	
1N2620B	0.191	-55 , 0, ± 25 , ± 75 , ± 100 , ± 150	0.01	15
1N2621B	0.095		0.005	
1N2622B	0.038		0.002	
1N2623B	0.019		0.001	
1N2624B	0.010		0.0005	

*Tighter-tolerance units available on special request.

CAPACITANCE (C) = 75 to 200 pF @ 90% of V_Z

FORWARD BREAKDOWN VOLTAGE (V_F) = 100 to 800 V



Quality Semi-Conductors